

isc Silicon NPN Darlington Power Transistor

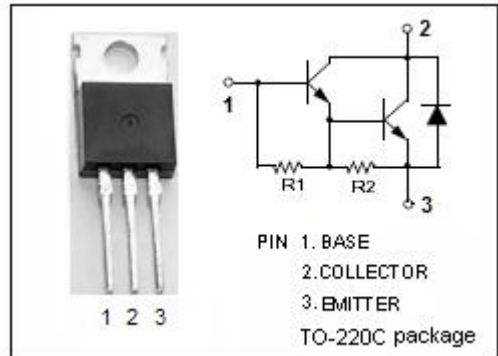
TIP132

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = 4A$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(\text{sat})} = 2.0V(\text{Max}) @ I_C = 4A$
- Complement to Type TIP137
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

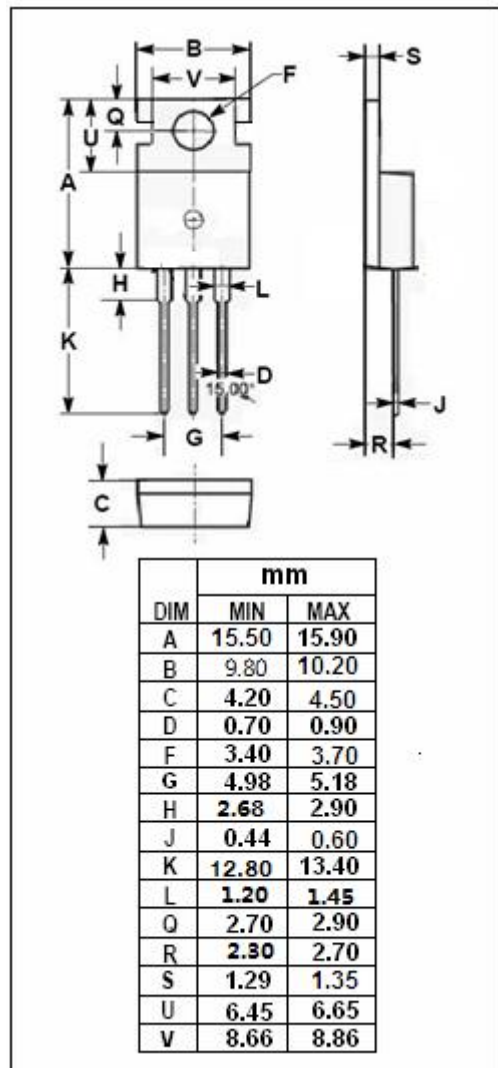
APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	12	A
I_B	Base Current- Continuous	0.3	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	70	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{th-j-c}	Thermal Resistance, Junction to Case	1.785	$^\circ\text{C/W}$
R_{th-j-a}	Thermal Resistance, Junction to Ambient	63.5	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 30mA, I _B = 0	100		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 16mA		2.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 6A, I _B = 30mA		3.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A; V _{CE} = 4V		2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 100V, I _E = 0		0.2	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 50V, I _B = 0		0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		5	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 4V	500		
h _{FE-2}	DC Current Gain	I _C = 4A; V _{CE} = 4V	1000	15000	